

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	("20040155341").PN.	USPAT	OR	OFF	2006/03/08 19:14
L2	1	("20040155341").PN.	US-PGPUB; USPAT	OR	OFF	2006/03/08 19:14
L3	1172	257/752	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 19:17
L4	3452	((257/374) or (257/499) or (257/506) or (257/510) or (257/513) or (257/521) or (257/752)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/08 19:21
L5	41	4 and ((polish\$3 with (implant\$5 or dop\$3 or (implant\$5 with ((non adj dopant\$1) or (nondopant\$1)))) same (insulat\$3 or dielectric or fill\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 19:23
L6	1310	257/510	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 19:31
L7	2764	257/751	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 19:31
S1	2	apparatus\$2 same (barrier near2 (layer or film)) same trench\$2 same (dielectric near2 (layer or film)) same ((ion near2 implant\$5) or dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 17:03
S2	1107	apparatus\$2 and (barrier near2 (layer or film)) and trench\$2 and (dielectric near2 (layer or film)) and ((ion near2 implant\$5) or dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:43
S3	5	apparatus\$2 same((barrier near2 (layer or film)) and trench\$2 and (dielectric near2 (layer or film)) and ((ion near2 implant\$5) or dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:05

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S4	9	("5897368" "6110817" "6218303" "6239021" "6258695" "6300236" "6340633" "6342447" "6352938" "2001/0010401").PN.	USPAT	OR	OFF	2004/09/10 16:07
S5	1373	apparatus\$2 near5 trench\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:12
S6	2500	apparatus\$2 with trench\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:12
S7	62	(apparatus\$2 with trench\$2) and (barrier near2 (layer or film)) and (dielectric near2 (layer or film))and ((ion near2 implant\$5) or dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 20:01
S8	108	isaac-stanetta.xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:29
S9	4	"6713385"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 17:04
S10	3043	((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/08 09:16
S11	4	(((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.) and (apparatus\$2 with trench\$2) and (barrier near2 (layer or film)) and (dielectric near2 (layer or film))and ((ion near2 implant\$5) or dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 20:01

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S12	194	apparatus same ((trench\$3 or groov\$3) near3 (silicon near2 (wafer\$1 or substrate\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 12:58
S13	30	S12 and (((ion near2 implant\$5) or dop\$3) same (dielectric or insulat\$3 or fill\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:05
S14	4230	apparatus same (((ion near2 implant\$5) or dop\$3) same (dielectric or insulat\$3 or fill\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:17
S15	46	S14 and ((trench\$3 or groov\$3) near3 (silicon near2 (wafer\$1 or substrate\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:09
S16	2764	(((ion near2 implant\$5) or dop\$3) near3 (dielectric or insulat\$3 or fill\$3)) same (trench\$3 or groov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 09:45
S17	383	S16 and apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:19
S18	360	S17 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:20
S19	1566	(((ion near2 implant\$5) or dop\$3) near3 (dielectric or insulat\$3)) same (trench\$3 or groov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:39

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S20	232	S19 and apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:21
S21	221	S20 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:21
S22	1161	((ion near2 implant\$5) or dop\$3) near3 ((dielectric or insulat\$3) near2 (layer\$1 or film\$1)) same (trench\$3 or groov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 15:22
S23	154	S22 and apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 15:23
S24	3212	((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 13:29
S25	2089	S24 and (trench\$2 or groov\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:43
S26	2021	S25 and (((ion near2 implant\$5) or dop\$3) near5 ((trench\$2 or groov\$2) near2 fill\$3) or dielectric or insulat\$3 or fill\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:52
S27	1631	S26 and (planar\$7 or (cmp or (chemical near2 polish\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:49
S28	367	S27 and nitrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:50

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S29	2021	S25 and (((ion near2 implant\$5) or dop\$3) near ((trench\$2 or groov\$2) near2 fill\$3) or dielectric or insulat\$3 or fill\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:52
S30	3301	((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 11:45
S31	24	S30 and ((ion\$1 or (ion near implant\$5) or dop\$3) near3 ((dielectric or insulat\$3) near2 (trench\$2 or groov\$2 or apeture\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 11:48
S32	3516	((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/08 09:16
S33	3082	(((ion near2 implant\$5) or dop\$3) near3 (dielectric or insulat\$3 or fill\$3)) same (trench\$3 or groov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 09:45
S34	146	S32 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 09:45
S35	13	S34 and ((high\$3 or increas\$3) near2 etch\$3 near rate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 09:46
S36	7024	((438/221) or (438/296) or (438/359) or (438/423) or (438/424) or (438/433) or (438/449) or (438/527) or (438/528) or (438/692) or (438/700)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/07 18:25

EAST Search History

S37	144	S36 and (((ion near2 implant\$5) or dop\$3) near3 (dielectric or insulat\$3)) same (trench\$3 or groov\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:46
S38	234	S36 and (((ion near2 implant\$5) or dop\$3) near3 (dielectric or insulat\$3 or fill\$3)) same (trench\$3 or groov\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:46
S39	16205	"10" and ("CMP" or planar\$7) near5 (trench\$2 or groove\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:47
S40	97	S38 and ("CMP" or planar\$7) near5 (trench\$2 or groove\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:47

EAST Search History

S41	108	("3629023" "3979239" "4010583" "4193226" "4256535" "4261791" "4373991" "4393628" "4505720" "4600469" "4677043" "4768883" "4778532" "4789648" "4811522" "4879258" "4933715" "4944836" "4954141" "4956313" "4962423" "4968381" "4986878" "5032203" "5057462" "5064683" "5084419" "5209816" "5262354" "5273558" "5288333" "5294570" "5312777" "5320706" "5320978" "5340370" "5346584" "5362668" "5362669" "5363550" "5376482" "5389194" "5389579" "5392361" "5395801" "5397741" "5401691" "5406111" "5421769" "5435772" "5436488" "5441094" "5453639" "5459096" "5468983" "5486265" "5492858" "5494857" "5503962" "5525840" "5531861" "5541427" "5551986" "5573633" "5578523" "5591239" "5595937" "5602423" "5607345" "5616513" "5629242" "5643406" "5643823" "5643836" "5652176" "5656097" "5662769" "5664990" "5665202" "5666985" "5676587" "5695572" "5702977" "5721172" "5728308" "5776808" "5782675" "5786260" "5837612" "5906532" "5919082" "5928959" "5943590" "5952687" "5963841" "5972124" "5972792" "6010964" "6016000" "6042996" "6063689" "6136713" "6143663" "6200896" "6218267" "6227956" "6265315" "6435944").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/08 13:48
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EAST Search History

S42	0	("6969684").URPN.	USPAT	OR	OFF	2005/12/08 13:51
S43	2	("6514833" "6576558").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/08 13:52
S44	24	("4577395" "4589193" "4654120" "4722910" "5021355" "5059550" "5212106" "5215937" "5229316" "5258332" "5275965" "5281550" "5292683" "5298110" "5300447" "5396096" "5408116" "5413945" "5482878" "5506168" "5521422" "5607875" "5677229" "5741738").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/08 13:56
S45	11	("6084276").URPN.	USPAT	OR	OFF	2005/12/08 13:58
S46	3	("4571819" "5316965" "5616513").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/08 14:01
S47	15	("5902127").URPN.	USPAT	OR	OFF	2005/12/08 15:08
S48	249	(438/433).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 15:09
S49	3	("20020098661" "20020137306" "6221734").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/08 15:13
S50	7240	((438/221) or (438/296) or (438/359) or (438/423) or (438/424) or (438/433) or (438/449) or (438/527) or (438/528) or (438/692) or (438/700)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/08 17:45
S51	167	S50 and ((polish\$3 with (implant\$5 or dop\$3)) same (insulat\$3 or dielectric or fill\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 17:49

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S52	7990	((438/42) or (438/221) or (438/296) or (438/359) or (438/423) or (438/424) or (438/433) or (438/449) or (438/524) or (438/527) or (438/528) or (438/692) or (438/700) or (438/734) or (438/924)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/08 17:56
S53	172	S52 and ((polish\$3 with (implant\$5 or dop\$3)) same (insulat\$3 or dielectric or fill\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 17:51
S54	172	S52 and ((polish\$3 with (implant\$5 or dop\$3 or (implant\$5 with ((non adj dopant\$1) or (nondopant\$1)))) same (insulat\$3 or dielectric or fill\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 19:21
S55	1692	(438/424).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/08 18:13
S56	2396	(438/692).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/08 18:24
S57	99	(438/924).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/08 18:26
S58	696	(257/E21.54).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/08 18:30
S59	1601	(257/E21.546).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/08 18:30